



Quad Complementary CMOS Analog Switch

FEATURES

- ±22-V Supply Voltage Rating
- TTL and CMOS Compatible Logic
- Low On-Resistance— $r_{DS(on)}$: 45 Ω
- Low Leakage— $I_{D(on)}$: 20 pA
- Single Supply Operation Possible
- Extended Temperature Range
- Fast Switching— t_{ON} : 85 ns

BENEFITS

- Low Charge Injection—Q: 1 pC
- Wide Analog Signal Range
- Simple Logic Interface
- Higher Accuracy
- Minimum Transients
- Reduced Power Consumption
- Low Cost

APPLICATIONS

- Industrial Instrumentation
- Test Equipment
- Communications Systems
- Computer Peripherals
- Portable Instruments
- Sample-and-Hold Circuits

DESCRIPTION

The versatile DG213 analog switch has two NC and two NO switches. It can be used in various configurations, including four single-pole single-throw (SPST), two single-pole double-throw (SPDT), one "T" switch, one DPDT, etc. This device is fabricated in a Vishay Siliconix' proprietary high-voltage silicon gate CMOS process, resulting in lower on-resistance, lower leakage, higher speed, and lower power consumption.

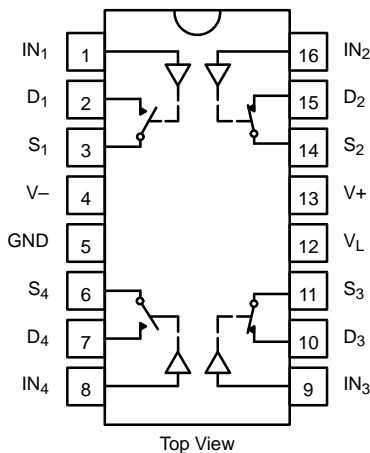
injection compensation design minimizes switching transients. These switches can handle up to ±22 V, and have an improved continuous current rating of 30 mA. An epitaxial layer prevents latchup.

All switches feature true bi-directional performance in the on condition, and will block signals to the supply levels in the off condition.

This analog switch was designed for a wide variety of general purpose applications in telecommunications, instrumentation, process control, computer peripherals, etc. An improved charge

For additional information, please refer to Application Note AN208 (FaxBack document #70606).

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE		
Logic	SW ₁ , SW ₄	SW ₂ , SW ₃
0	OFF	ON
1	ON	OFF

Logic "0" ≤ 0.8 V
Logic "1" ≥ 2.4 V

ORDERING INFORMATION		
Temp Range	Package	Part Number
-40 to 85°C	16-Pin Plastic DIP	DG213DJ
	16-Pin Narrow SOIC	DG213DY
	16-Pin TSSOP	DG213DQ



ABSOLUTE MAXIMUM RATINGS

Voltages Referenced to V-

V+	44 V
GND	25 V
Digital Inputs ^a V _S , V _D	(V-) -2 V to (V+) +2 V or 30 mA, whichever occurs first
Current, Any Terminal	30 mA
Peak Current, S or D (Pulsed at 1 ms, 10% duty cycle max)	100 mA
Storage Temperature	-65 to 125°C

Power Dissipation (Package)^b

16-Pin Plastic DIP ^c	470 mW
16-Pin Narrow SOIC ^d	640 mW
16-Pin TSSOP ^d	500 mW

- Notes:
- Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
 - All leads welded or soldered to PC Board.
 - Derate 6.5 mW/°C above 75°C
 - Derate 7.6 mW/°C above 75°C

SPECIFICATIONS							
Parameter	Symbol	Test Conditions Unless Otherwise Specified V+ = 15 V, V- = -15 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V ^e	Temp ^a	D Suffix -40 to 85°C			Unit
				Min ^c	Typ ^b	Max ^c	
Analog Switch							
Analog Signal Range ^d	V _{ANALOG}		Full	V-		V+	V
Drain-Source On-Resistance	r _{DS(on)}	V _D = ±10 V, I _S = 1 mA	Room		45	60	Ω
r _{DS(on)} Match	Δr _{DS(on)}		Room		1	2	
Source Off Leakage Current	I _{S(off)}	V _S = ±14 V, V _D = ∓14 V	Room	-0.5	±0.01	0.5	nA
Drain Off Leakage Current	I _{D(off)}	V _D = ±14 V, V _S = ∓14 V	Room	-0.5	±0.01	0.5	
Drain On Leakage Current	I _{D(on)}	V _S = V _D = 14 V	Room	-0.5	±0.02	0.5	
Digital Control							
Input Voltage High	V _{INH}		Full	2.4			V
Input Voltage Low	V _{INL}		Full			0.8	
Input Current	I _{INH} or I _{INL}	V _{INH} or V _{INL}	Full	-1		1	μA
Input Capacitance	C _{IN}		Room		5		pF
Dynamic Characteristics							
Turn-On Time	t _{ON}	V _S = 10 V See Figure 2	Room		85	130	ns
Turn-Off Time	t _{OFF}		Room		55	100	
Break-Before-Make Time Delay	t _D	V _S = 10 V, See Figure 3	Room	15	25		
Charge Injection	Q	C _L = 1000 pF, V _g = 0 V, R _g = 0 Ω	Room		1		pC
Source-Off Capacitance	C _{S(off)}	V _S = 0 V, f = 1 MHz	Room		5		pF
Drain-Off Capacitance	C _{D(off)}		Room		5		
Channel On Capacitance	C _{D(on)}	V _D = V _S = 0 V, f = 1 MHz	Room		16		
Off Isolation	OIRR	C _L = 15 pF, R _L = 50 Ω V _S = 1 V _{RMS} , f = 100 kHz	Room		90		dB
Channel-to-Channel Crosstalk	X _{TALK}		Room		95		



SPECIFICATIONS							
Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 15\text{ V}$, $V_- = -15\text{ V}$ $V_L = 5\text{ V}$, $V_{IN} = 2.4\text{ V}$, 0.8 V^e	Temp ^a	D Suffix -40 to 85°C			Unit
				Min ^c	Typ ^b	Max ^c	
Power Supply							
Positive Supply Current	I+	$V_{IN} = 0\text{ or }5\text{ V}$	Room Full			1 5	μA
Negative Supply Current	I-		Room Full	-1 -5			
Logic Supply Current	I _L		Room Full			1 5	
Power Supply Range for Continuous Operation	V _{OP}		Full	±3		±22	V

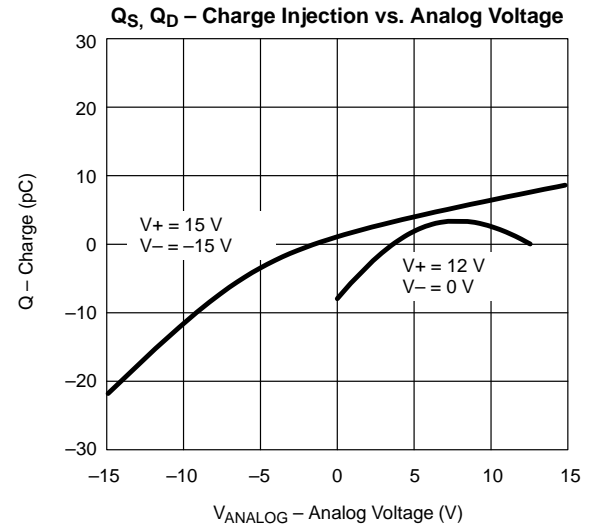
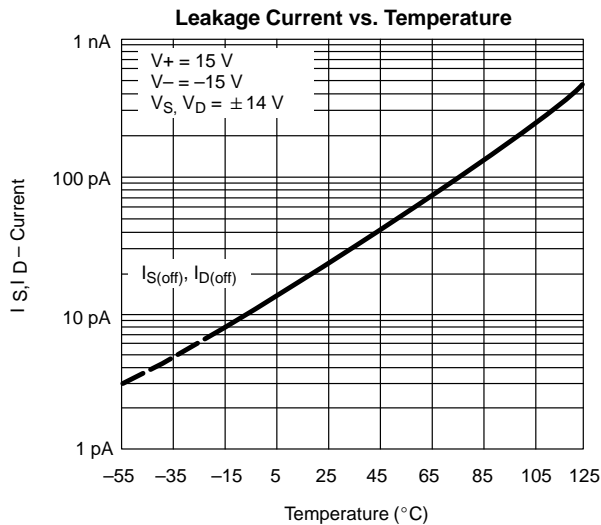
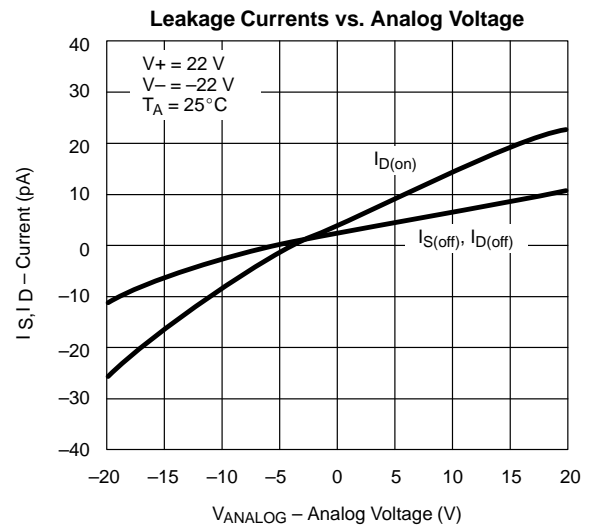
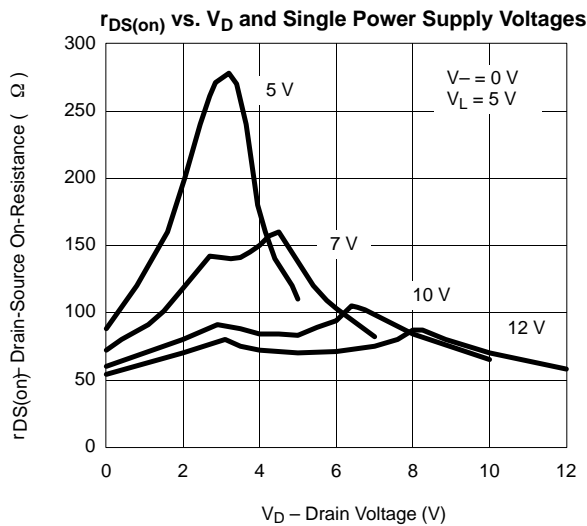
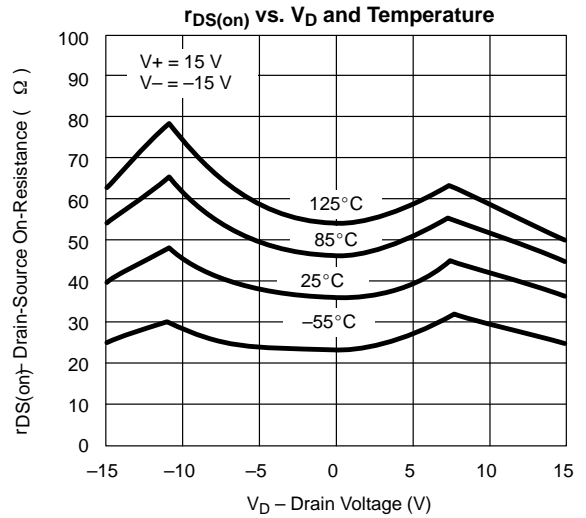
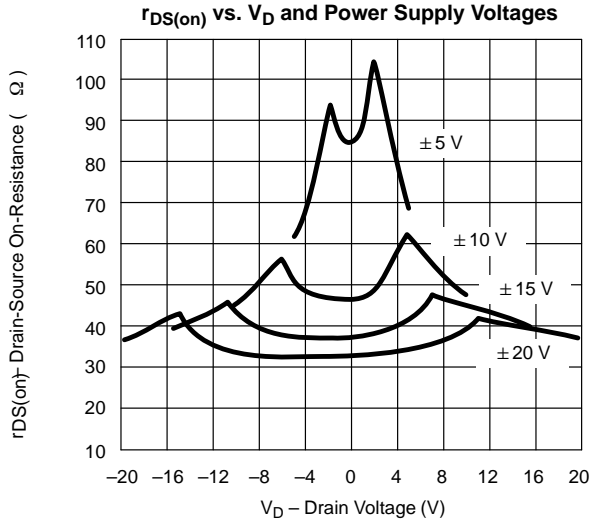
SPECIFICATIONS FOR UNIPOLAR SUPPLY							
Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 12\text{ V}$, $V_- = 0\text{ V}$ $V_L = 5\text{ V}$, $V_{IN} = 2.4\text{ V}$, 0.8 V^e	Temp ^a	D Suffix -40 to 85°C			Unit
				Min ^c	Typ ^b	Max ^c	
Analog Switch							
Analog Signal Range ^d	V _{ANALOG}		Full	V-		V+	V
Drain-Source On-Resistance	r _{DS(on)}	$V_D = 3\text{ V}$, 8 V , $I_S = 1\text{ mA}$	Room Full		90	110 140	Ω
Dynamic Characteristics							
Turn-On Time	t _{ON}	See Figure 2	Room		125	200	ns
Turn-Off Time	t _{OFF}		Room		45	100	
Break-Before-Make Time Delay	t _D	$V_S = 8\text{ V}$, See Figure 3	Room	50	80		
Charge Injection	Q	$C_L = 1\text{ nF}$, $V_{gen} = 6\text{ V}$, $R_{gen} = 0\ \Omega$	Room		4		pC
Power Supply							
Positive Supply Current	I+	$V_{IN} = 0\text{ or }5\text{ V}$	Room Full			1 5	μA
Negative Supply Current	I-		Room Full	-1 -5			
Logic Supply Current	I _L		Room Full			1 5	
Power Supply Range for Continuous Operation	V _{OP}		Full	+3		+40	V

Notes:

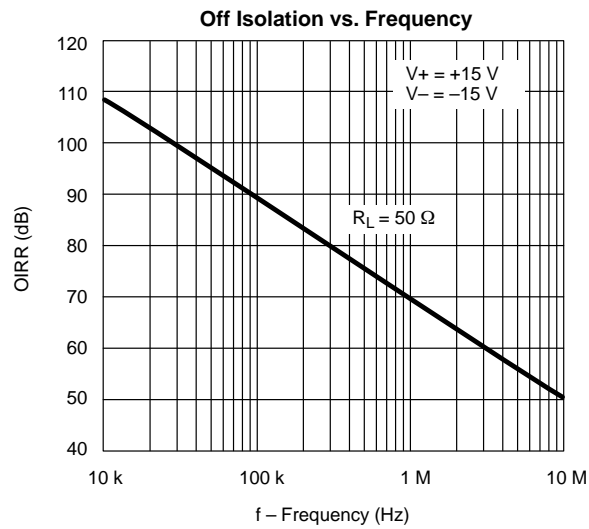
- a. Room = 25°C, Full = as determined by the operating temperature suffix.
- b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- d. Guaranteed by design, not subject to production test.
- e. V_{IN} = input voltage to perform proper function.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



SCHEMATIC DIAGRAM (TYPICAL CHANNEL)

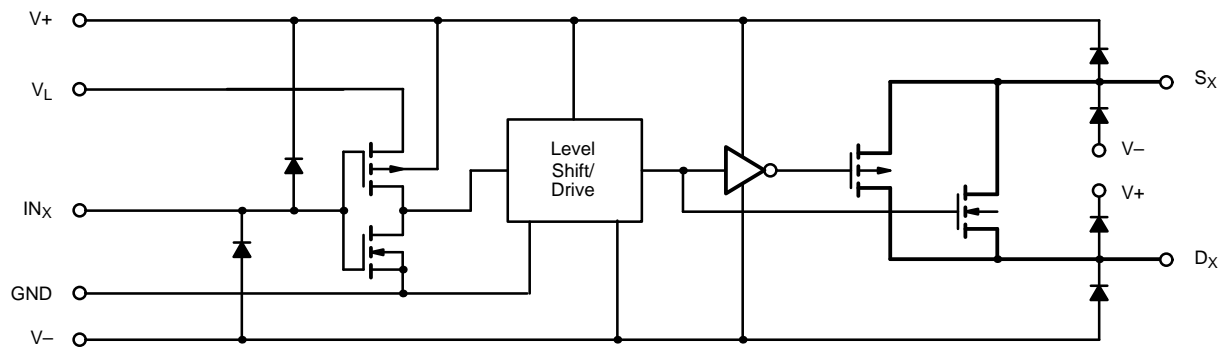


FIGURE 1.

TEST CIRCUITS

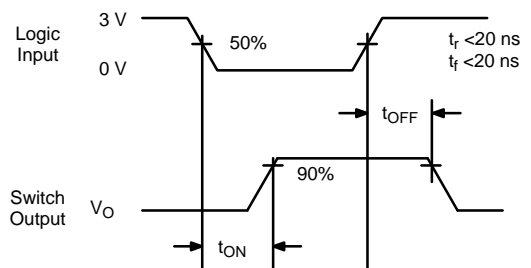
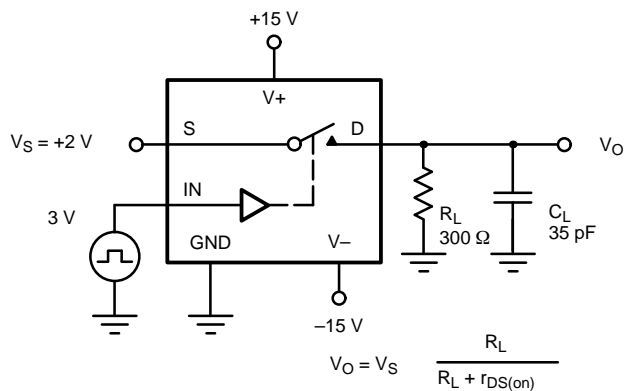
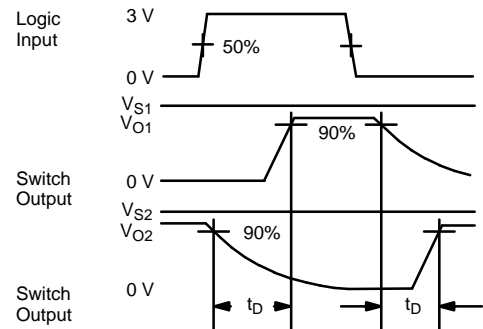
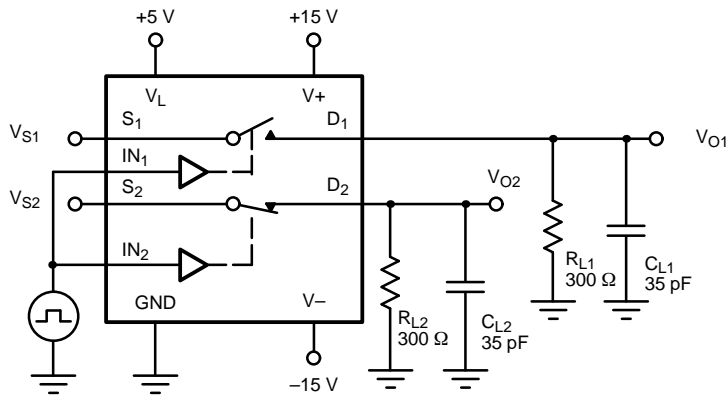


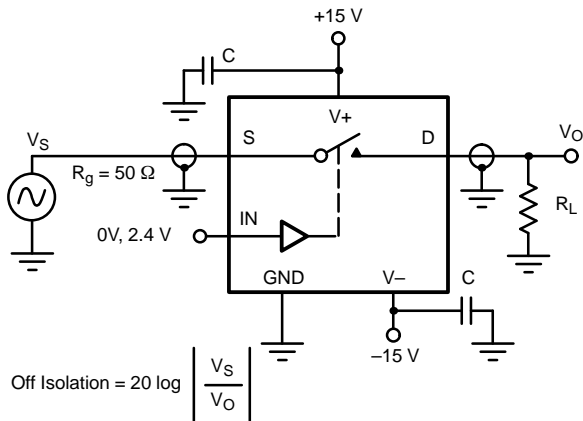
FIGURE 2. Switching Time

TEST CIRCUITS



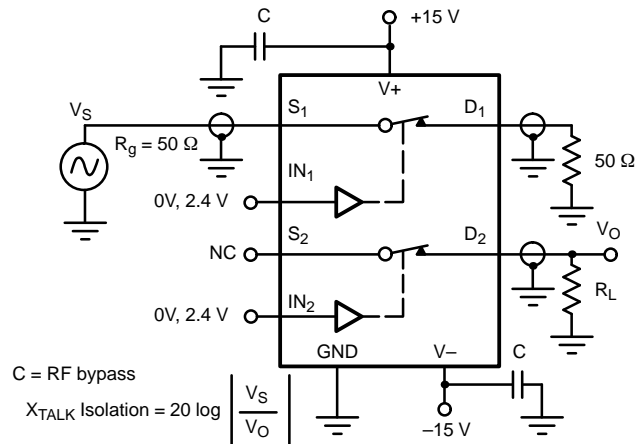
C_L (includes fixture and stray capacitance)

FIGURE 3. Break-Before-Make



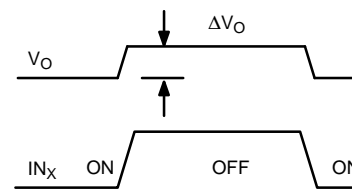
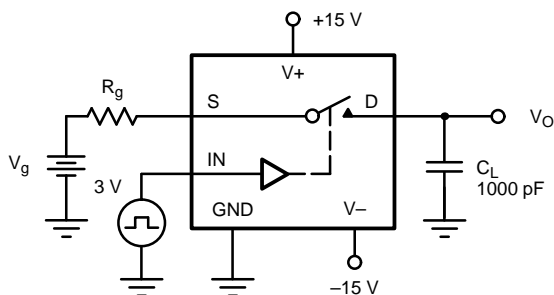
$$\text{Off Isolation} = 20 \log \left| \frac{V_S}{V_O} \right|$$

FIGURE 4. Off Isolation



$C = \text{RF bypass}$
 $X_{\text{TALK}} \text{ Isolation} = 20 \log \left| \frac{V_S}{V_O} \right|$

FIGURE 5. Channel-to-Channel Crosstalk



ΔV_O = measured voltage error due to charge injection
 The charge injection in coulombs is $Q = C_L \times \Delta V_O$

FIGURE 6. Charge Injection

APPLICATIONS

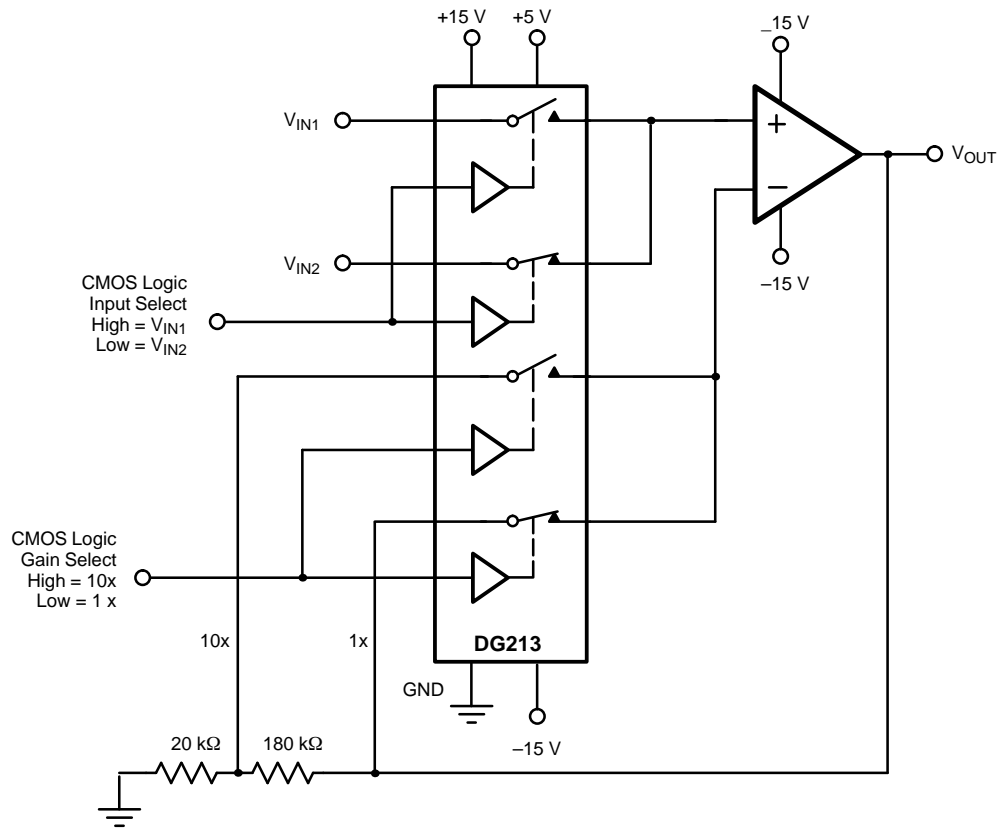


FIGURE 7. Low Power Non-Inverting Amplifier with Digitally Selectable Inputs and Gain